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July 2008 IGBT®

FGH40N120AN 1200V NPT IGBT

Features

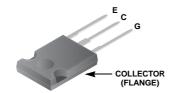
- · High speed switching
- Low saturation voltage : $V_{CE(sat)} = 2.6 \text{ V} @ I_C = 40 \text{A}$
- · High input impedance
- · RoHS complaint

Applications

Induction Heating, UPS, AC & DC motor controls and general purpose inverters.

Description

Employing NPT technology, Fairchild's AN series of IGBTs provides low conduction and switching losses. The AN series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).





Absolute Maximum Ratings

Symbol	Parameter		FGH40N120AN	Units
V _{CES}	Collector-Emitter Voltage		1200	V
V _{GES}	Gate-Emitter Voltage		±25	V
1	Collector Current	@T _C = 25°C	64	Α
l _C	Collector Current	@T _C = 100°C	40	Α
I _{CM(1)}	Pulsed Collector Current		160	Α
D	Maximum Power Dissipation	@T _C = 25°C	417	W
P_{D}	Maximum Power Dissipation	@T _C = 100°C	167	W
SCWT	Short Circuit Withstand Time, V _{CE} = 600V, V _{GE} = 15V, T _C = 125°C		10	μs
TJ	Operating Junction Temperature		-55 to +150	°C
T _{STG}	Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 seconds		300	°C

Notes

(1) Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction-to-Case		0.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGH40N120AN	FGH40N120AN	TO-247	=	=	30

Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Off Charact	reristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V$, $I_C = 1mA$	1200			V
BV _{CES} / ΔT _J	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V$, $I_C = 1mA$		0.6		V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$			1	mA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$			±250	nA
On Charact	eristics					
V _{GE(th)}	G-E Threshold Voltage	$I_{C} = 250 \mu A, V_{CE} = V_{GE}$	3.5	5.5	7.5	V
OL(III)	j ,	I _C = 40A, V _{GE} = 15V		2.6	3.2	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	$I_C = 40A, V_{GE} = 15V,$ $T_C = 125^{\circ}C$		2.9		V
		I _C = 64A, V _{GE} = 15V		3.15		V
Dvnamic Cl	haracteristics	,		l		
C _{ies}	Input Capacitance			3200		pF
C _{oes}	Output Capacitance	$V_{CE} = 30V, V_{GE} = 0V$		370		pF
C _{res}	Reverse Transfer Capacitance	f = 1MHz		125		pF
Switching (Characteristics			•	•	•
t _{d(on)}	Turn-On Delay Time			15		ns
t _r	Rise Time			20		ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 600V, I_{C} = 40A,$		110		ns
t _f	Fall Time	$R_G = 5\Omega$, $V_{GE} = 15V$,		40	80	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 25°C		2.3	3.45	mJ
E _{off}	Turn-Off Switching Loss]		1.1	1.65	mJ
E _{ts}	Total Switching Loss]		3.4	5.1	mJ
t _{d(on)}	Turn-On Delay Time			20		ns
t _r	Rise Time			25		ns
t _{d(off)}	Turn-Off Delay Time	V_{CC} = 600V, I_{C} = 40A, R_{G} = 5 Ω , V_{GE} = 15V, Inductive Load, T_{C} = 125°C		120		ns
t _f	Fall Time			45		ns
E _{on}	Turn-On Switching Loss			2.5		mJ
E _{off}	Turn-Off Switching Loss			1.8		mJ
E _{ts}	Total Switching Loss			4.3		mJ
Qg	Total Gate charge	V 000V I 101		220		nC
Q _{ge}	Gate-Emitter Charge	$V_{CE} = 600V, I_{C} = 40A,$ $V_{GE} = 15V$		25		nC
Q _{gc}	Gate-Collector Charge	- GE = 10 t		130		nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

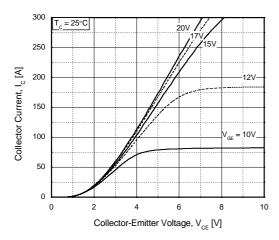


Figure 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

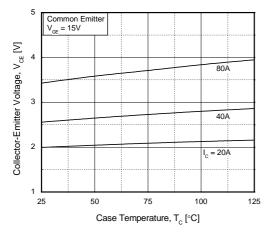


Figure 5. Saturation Voltage vs. V_{GE}

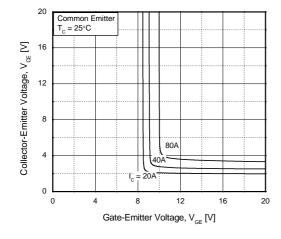


Figure 2. Typical Saturation Voltage Characteristics

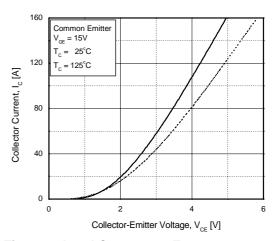


Figure 4. Load Current vs. Frequency

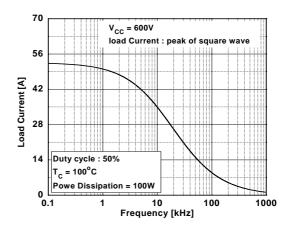
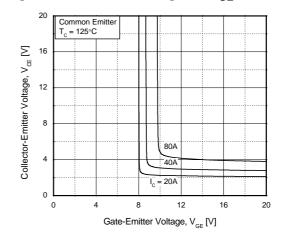


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics (Continued)

Figure 7. Capacitance Characteristics

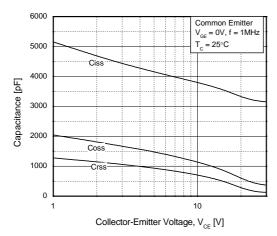


Figure 9. Turn-Off Characteristics vs. Gate Resistance

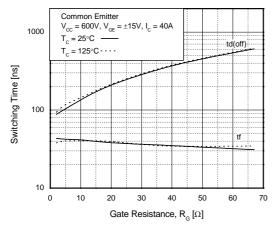


Figure 11. Turn-On Characteristics vs. Collector Current

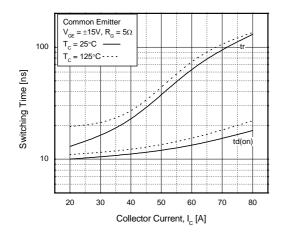


Figure 8. Turn-On Characteristics vs. Gate Resistance

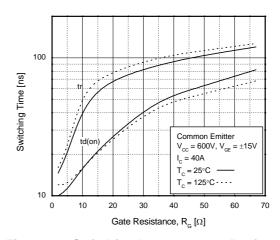


Figure 10. Switching Loss vs. Gate Resistance

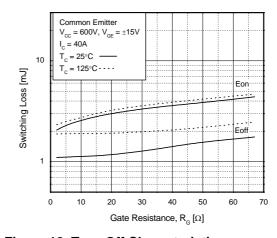
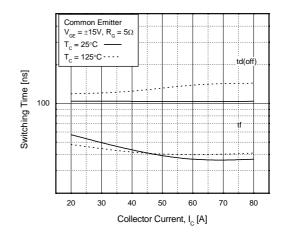


Figure 12. Turn-Off Characteristics vs. Collector Current



Typical Performance Characteristics (Continued)

Figure 13. Switching Loss vs. Collector Current

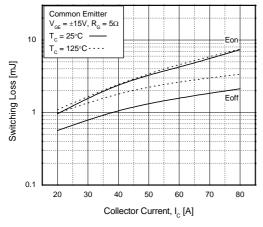


Figure 14. Gate Charge Characteristics

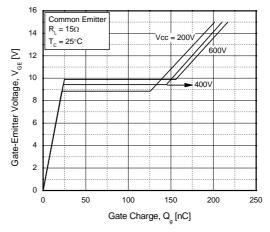


Figure 15. SOA Characteristics

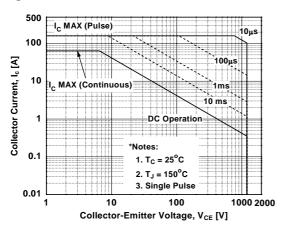


Figure 16. Turn-Off SOA

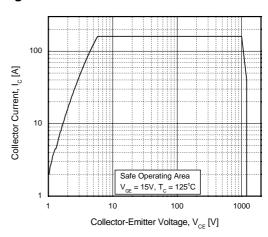
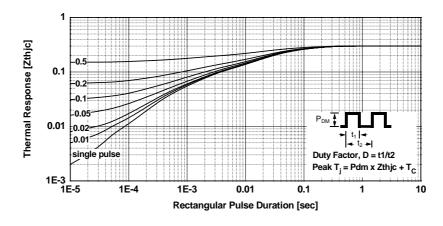
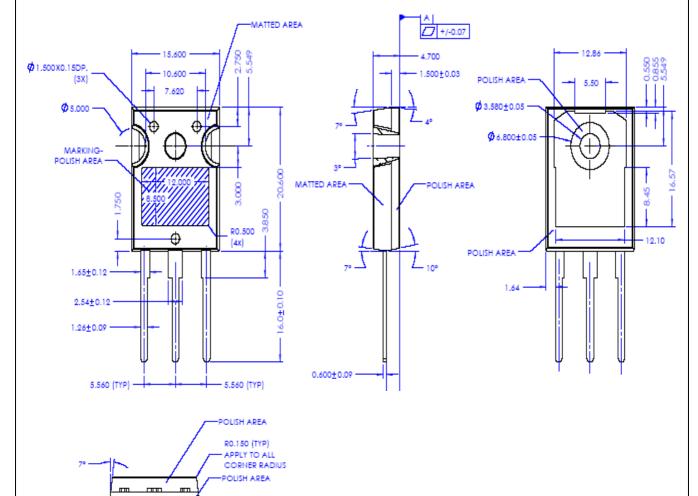


Figure 17. Transient Thermal Impedance of IGBT



Mechanical Dimensions

TO-247AB (FKS PKG CODE 001)



Dimensions in Millimeters





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